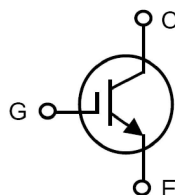


1200V XPT™ IGBT GenX4™

IXYK140N120A4

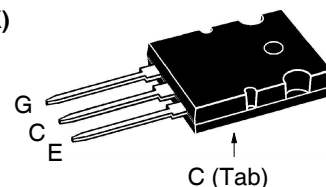
Ultra Low-V_{sat} IGBT for
up to 5kHz Switching



$$\begin{aligned} V_{CES} &= 1200V \\ I_{C110} &= 140A \\ V_{CE(sat)} &\leq 1.70V \\ t_{fi(typ)} &= 320ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	1200	V
V_{CGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	480	A
I_{LRMS}	Terminal Current Limit	160	A
I_{C110}	$T_C = 110^\circ\text{C}$	140	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	1200	A
SSOA	$V_{GE} = 15V, T_{VJ} = 125^\circ\text{C}, R_G = 2\Omega$	$I_{CM} = 280$	A
(RBSOA)	Clamped Inductive Load	$0.8 \cdot V_{CES}$	V
P_C	$T_C = 25^\circ\text{C}$	1500	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in
Weight		10	g

TO-264
(IXYK)



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for Low Conduction Losses
- Positive Thermal Coefficient of $V_{ce(sat)}$
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 4\text{mA}, V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 5 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$		1.34 1.50	1.70 V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	60	100	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		8300	pF
C_{oes}			470	pF
C_{res}			300	pF
$Q_{g(on)}$	$I_C = I_{C110}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		420	nC
Q_{ge}			68	nC
Q_{gc}			210	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 70\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1.5\Omega$ Note 2		52	ns
t_{ri}			47	ns
E_{on}			4.9	mJ
$t_{d(off)}$			590	ns
t_{fi}			320	ns
E_{off}			12.0	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 70\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1.5\Omega$ Note 2		44	ns
t_{ri}			42	ns
E_{on}			7.4	mJ
$t_{d(off)}$			710	ns
t_{fi}			530	ns
E_{off}			20.0	mJ
R_{thJC}				0.10 $^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

Littelfuse reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

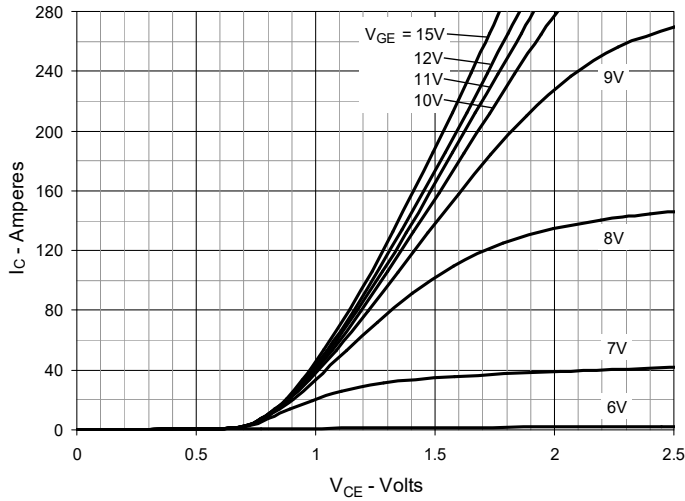


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

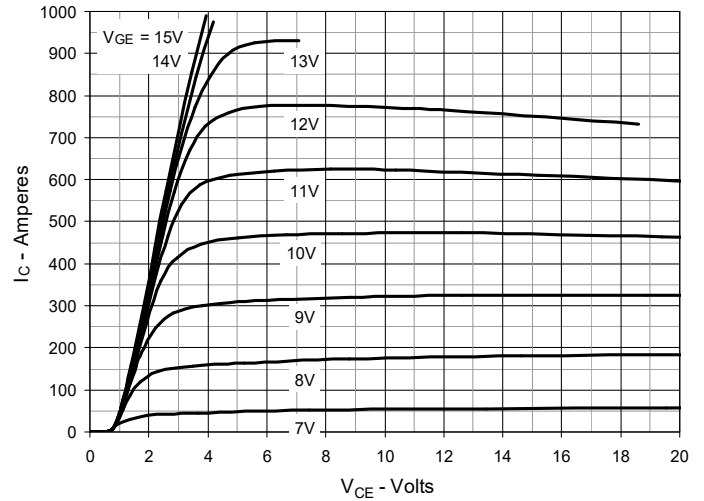


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

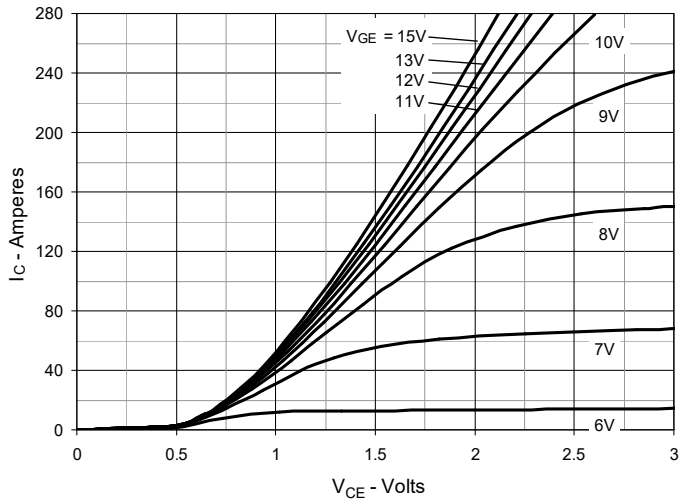


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

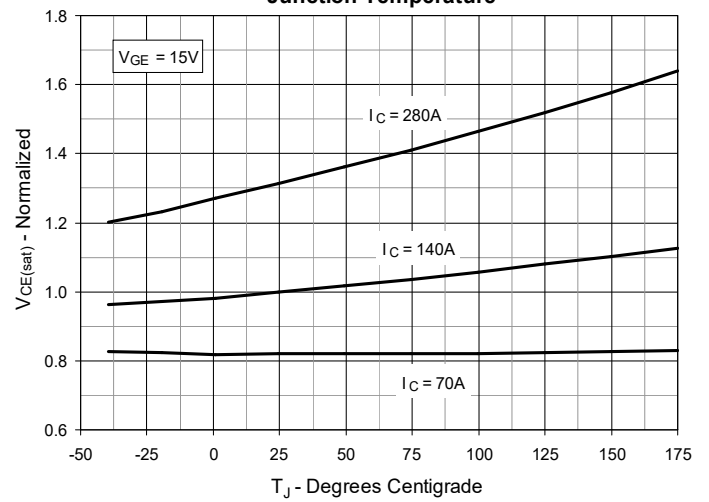


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

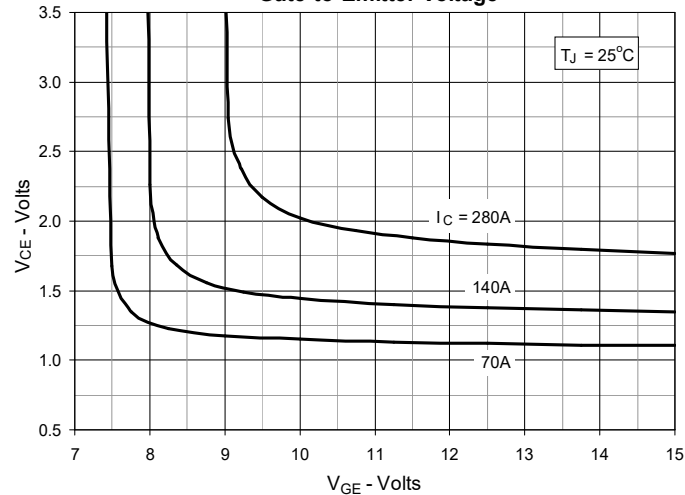


Fig. 6. Input Admittance

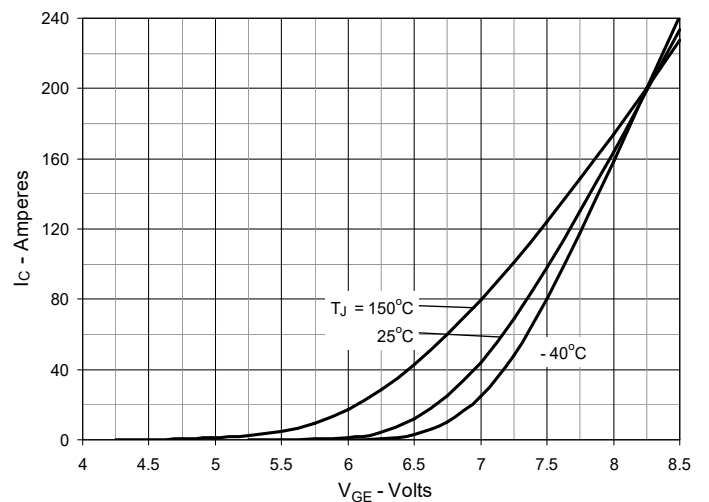


Fig. 7. Transconductance

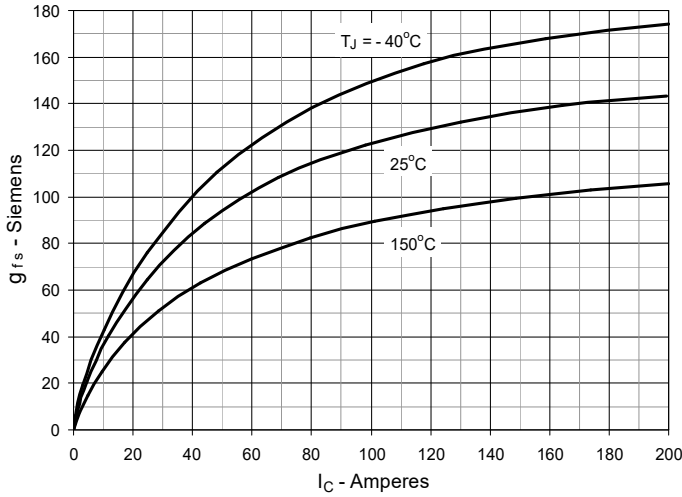


Fig. 8. Gate Charge

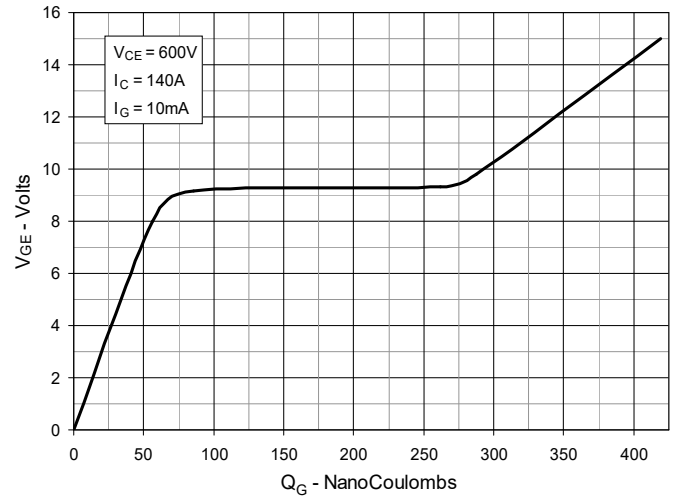


Fig. 9. Capacitance

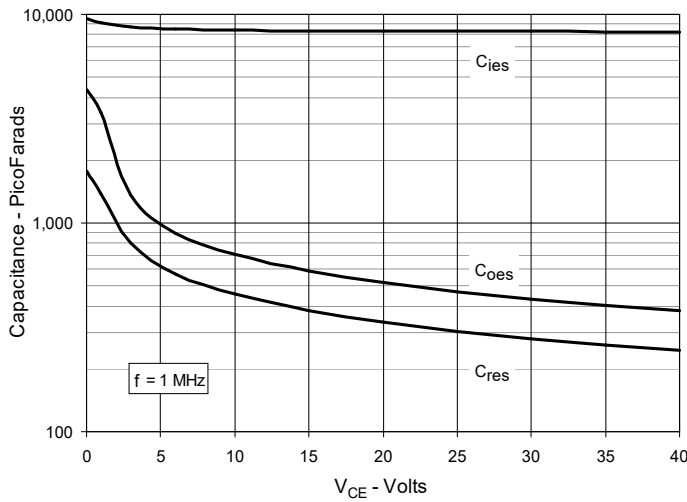


Fig. 10. Reverse-Bias Safe Operating Area

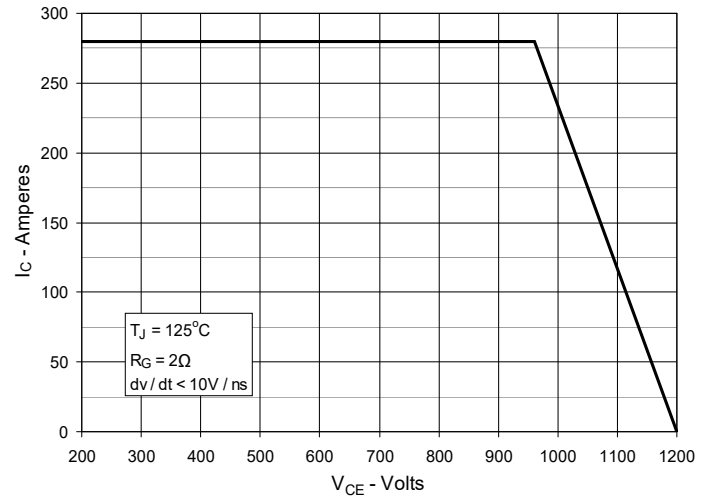


Fig. 11. Maximum Transient Thermal Impedance

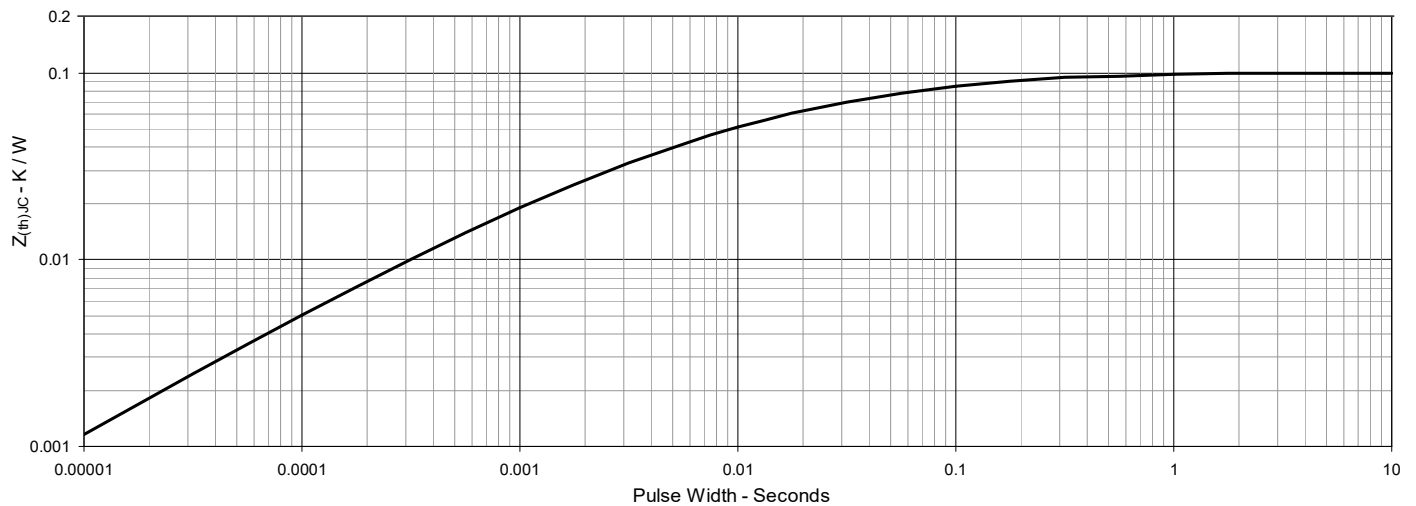


Fig. 12. Inductive Switching Energy Loss vs. Collector Current

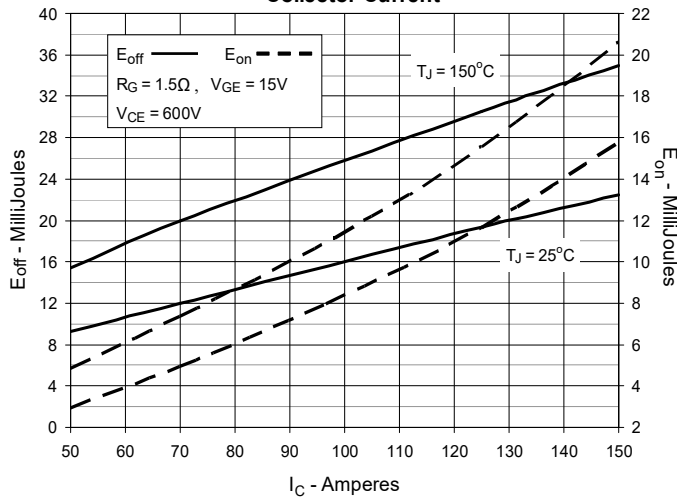


Fig. 13. Inductive Switching Energy Loss vs. Collector-Emitter Voltage

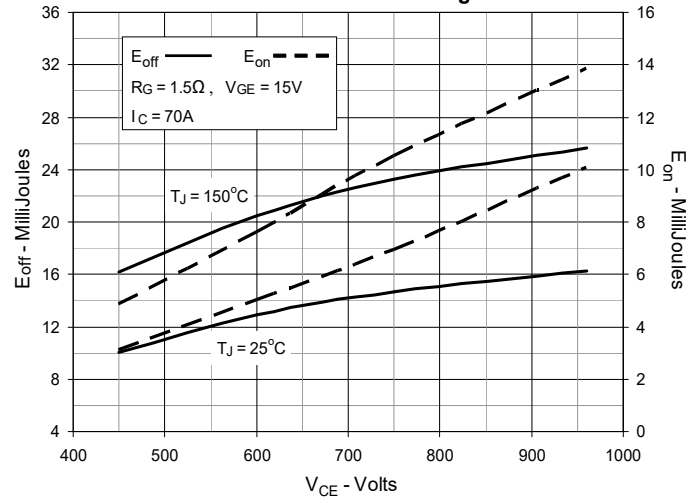


Fig. 14. Inductive Switching Energy Loss vs. Gate Resistance

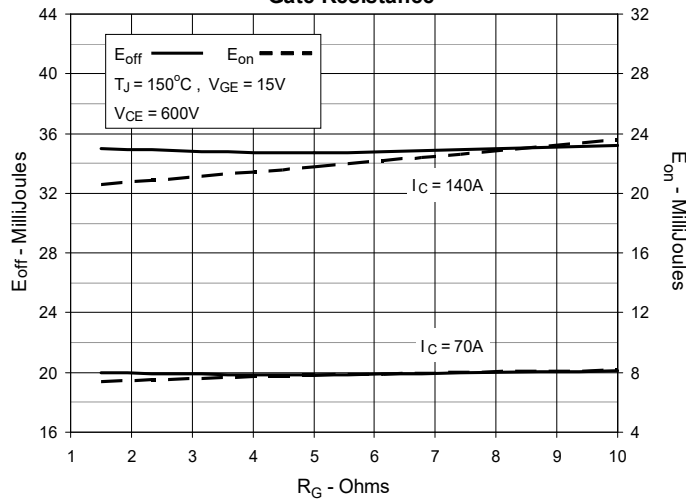


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

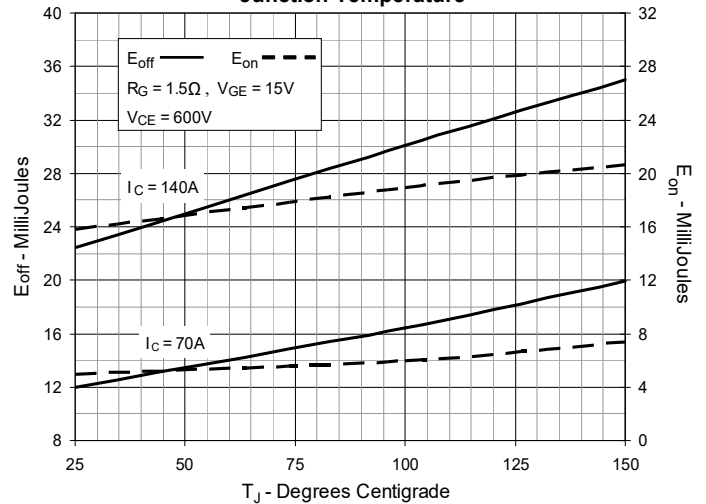


Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

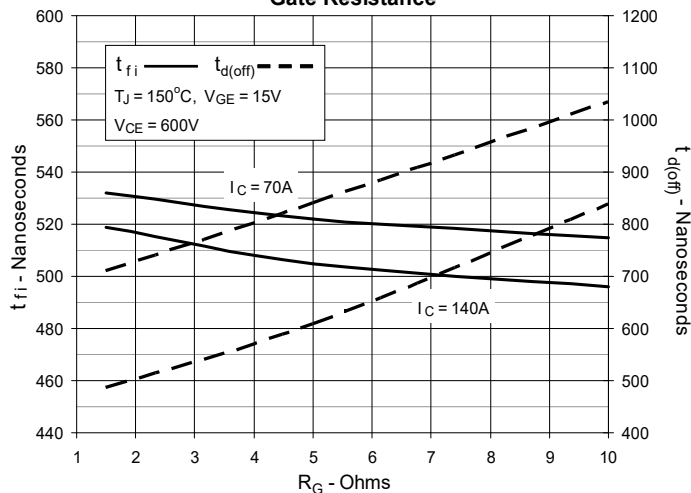


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

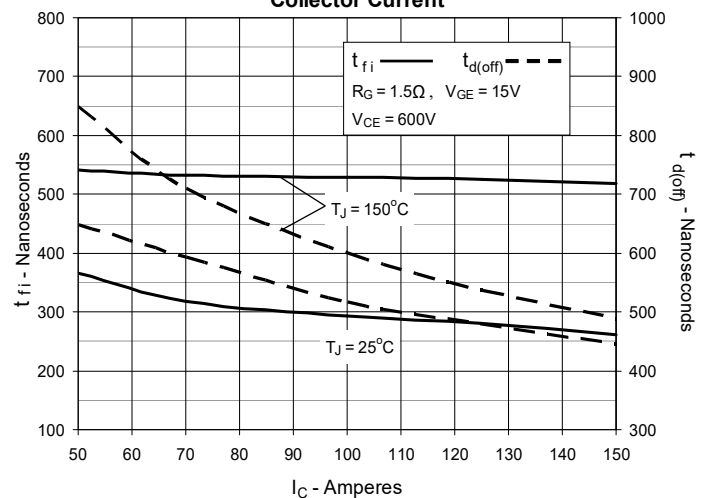


Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature

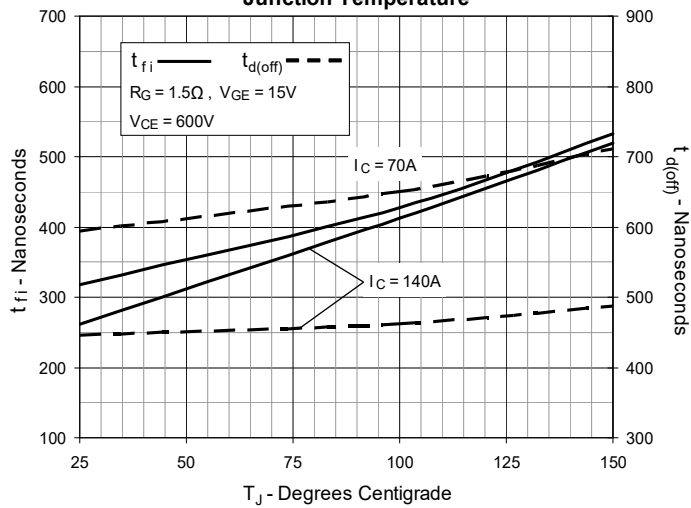


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

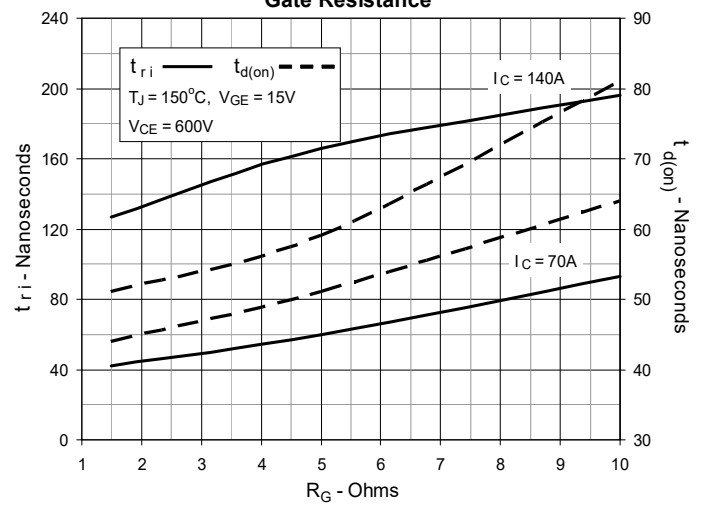


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

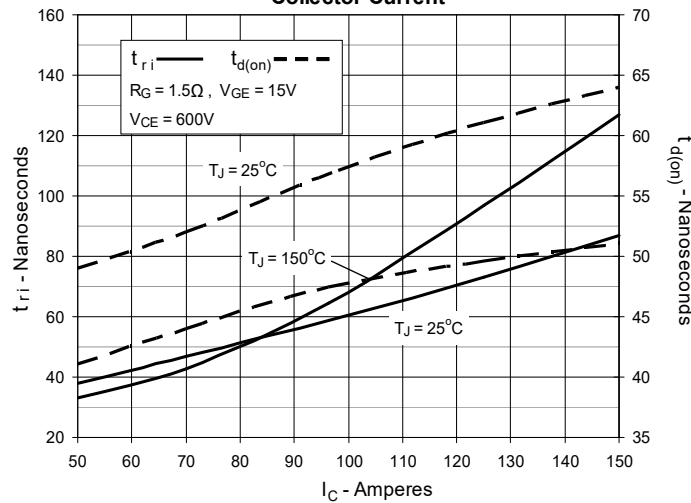
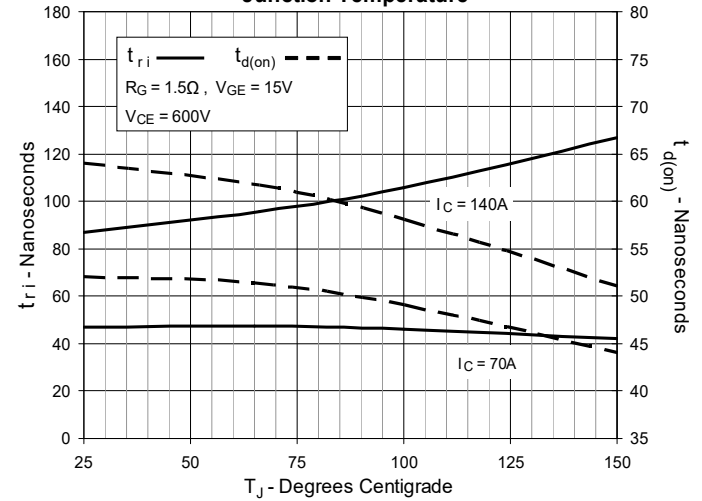
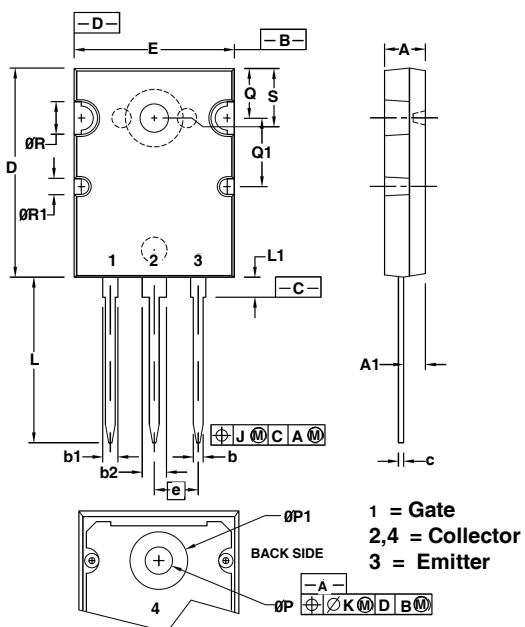


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature



TO-264 Outline


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ϕP	.122	.138	3.10	3.51
$\phi P1$	.270	.290	6.86	7.37
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ϕR	.155	.187	3.94	4.75
$\phi R1$	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

